

Silicon PNP Power Transistors

2SA1646

DESCRIPTION

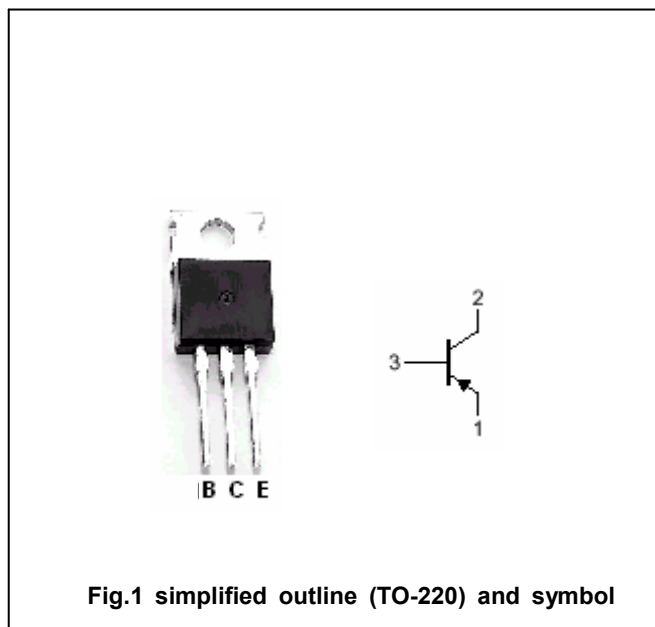
- With TO-220 package
- Fast switching speed
- Low collector saturation voltage

APPLICATIONS

- For use in switching power supplies,DC-DC converters,motor drivers,solenoid drivers, and other low-voltage power supply devices, as well as for high current switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-10	A
I_{CM}	Collector current-peak	$PW \leq 300\mu s$, duty cycle $\leq 10\%$	-20	A
I_B	Base current		-6	A
P_T	Total power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	40	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEsat-1}$	Collector-emitter saturation voltage	$I_C=-6A$; $I_B=-0.3A$			-0.3	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	$I_C=-8A$; $I_B=-0.4A$			-0.5	V
$V_{BE sat-1}$	Base-emitter saturation voltage	$I_C=-6A$; $I_B=-0.3A$			-1.2	V
$V_{BE sat-2}$	Base-emitter saturation voltage	$I_C=-8A$; $I_B=-0.4A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100V$; $I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-10	μA
h_{FE-1}	DC current gain	$I_C=-0.5A$; $V_{CE}=-2V$	100			
h_{FE-2}	DC current gain	$I_C=-2A$; $V_{CE}=-2V$	100		400	
h_{FE-3}	DC current gain	$I_C=-6A$; $V_{CE}=-2V$	60			
C_{OB}	Output capacitance	$I_E=0$; $V_{CB}=-10V$; $f=1MHz$		250		pF
f_T	Transition frequency	$I_C=-0.5A$; $V_{CE}=-10V$		150		MHz

Switching times

t_{on}	Turn-on time	$I_C=-6A$; $V_{CC}=-50V$ $I_{B1}=-I_{B2}=-0.3A$; $R_L=8.3\Omega$		0.3		μs
t_{stg}	Storage time			1.5		μs
t_f	Fall time			0.4		μs

◆ h_{FE-2} Classifications

M	L	K
100-200	150-300	200-400

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PACKAGE OUTLINE

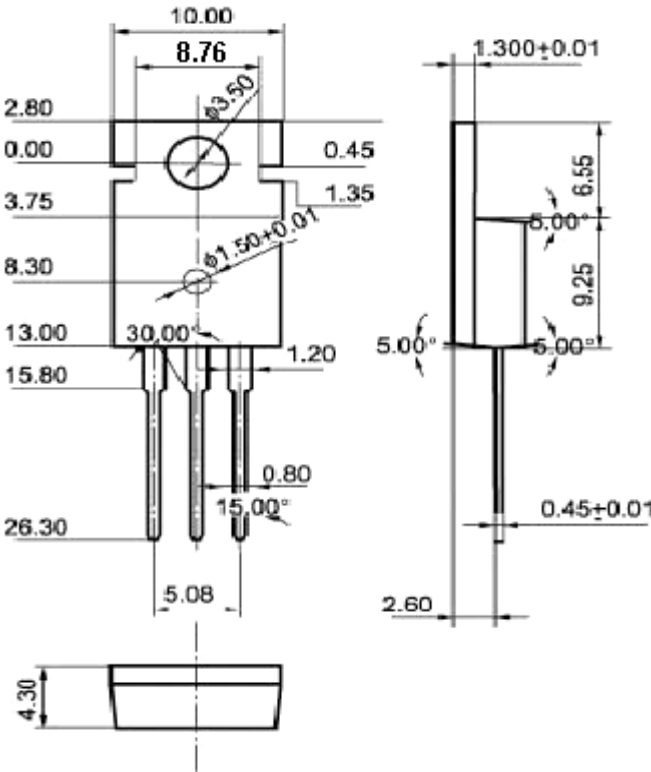


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)